

600 V
Size 30
5" Wafer

Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V _{FM}	Forward Voltage	1.7V Max.	T _J = 25°C, I _F = 15.0A
BV _R	Reverse Breakdown Voltage	600V Min.	T _J = 25°C, I _R = 250μA
I _{RM}	Reverse Leakage Current	10μA Max.	T _J = 25°C, V _R = 600V

Mechanical Data

Normal Backmetal Composition, Thickness:	Cr-Ni-Ag (1kA-4kA-6kA)
Normal Front Metal Composition, Thickness:	99% Al, 1% Si (3 microns)
Dimensions:	0.115" x 0.155"
Wafer Diameter:	125mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5161
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	See Die Outline drawing below
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : HFA15TB60

Die Outline

